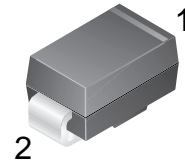




## US1A-US1M

## Features:

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

DO-214AC  
(SMA)

1.Cathode 2. Anode

**Absolute Maximum Ratings** ( $T_a=25^\circ\text{C}$  unless otherwise noted)

Ratings at  $25^\circ\text{C}$  ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Parameter	Symbols	US1A	US1B	US1D	US1G	US1J	US1K	US1M	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_c = 125^\circ\text{C}$	$I_{F(AV)}$	1							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	$I_{FSM}$	30							A
Maximum Instantaneous Forward Voltage at 1 A	$V_F$	1.0		1.3		1.65		V	
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Blocking Voltage $T_a = 125^\circ\text{C}$	$I_R$	5 100							$\mu\text{A}$
Maximum Reverse Recovery Time <sup>(1)</sup>	$t_{rr}$	50				75		ns	
Typical Thermal Resistance <sup>(2)</sup>	$R_{\theta JA}$	75							$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150							$^\circ\text{C}$

(1) Measured with  $I_F = 0.5\text{ A}$ ,  $I_R = 1\text{ A}$ ,  $I_{rr} = 0.25\text{ A}$ .

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Typical Characteristics

Fig.1 Forward Current Derating Curve

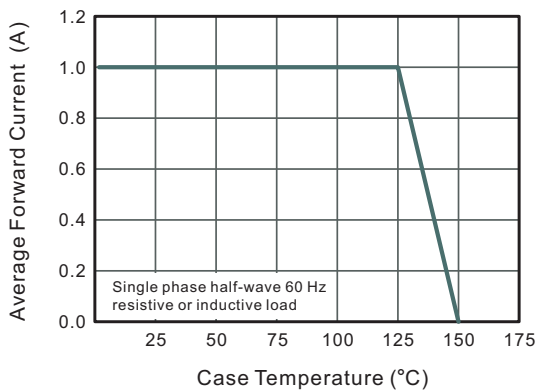


Fig.2 Typical Reverse Characteristics

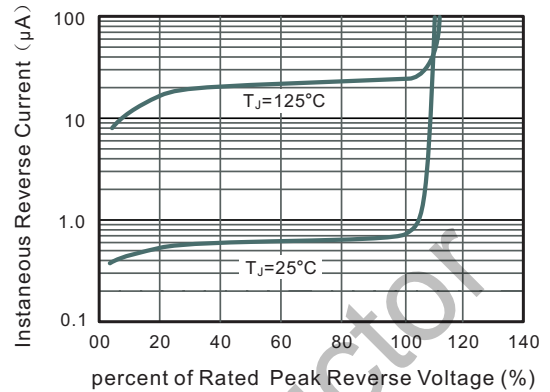


Fig.3 Typical Forward Characteristics

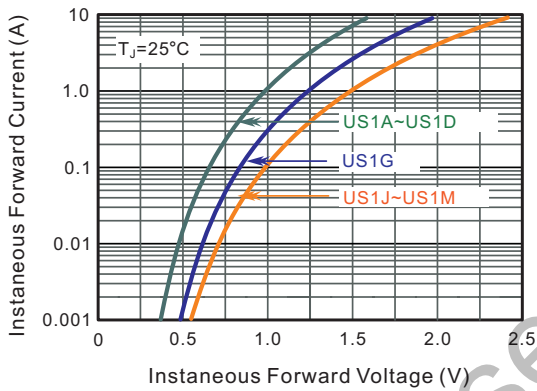
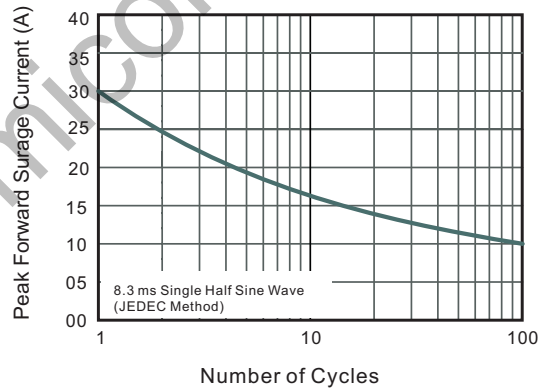


Fig.4 Maximum Non-Repetitive Peak Forward Surge Current



WildGoose Semiconductor

**Package Dimension****SMA**

Unit: mm

